

# NST3904DXV6T1G, NSVT3904DXV6T1G, NST3904DXV6T5G, SNST3904DXV6T5G



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## Dual General Purpose Transistor

The NST3904DXV6T1G device is a spin-off of our popular SOT-23/SOT-323 three-lead device. It is designed for general purpose amplifier applications and is housed in the SOT-563 six-lead surface mount package. By putting two discrete devices in one package, this device is ideal for low-power surface mount applications where board space is at a premium.

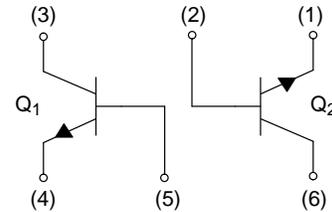
### Features

- $h_{FE}$ , 100–300
- Low  $V_{CE(sat)}$ ,  $\leq 0.4$  V
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- AEC-Q101 Qualified and PPAP Capable – NSVT3904DXV6T1G, SNST3904DXV6T5G
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These are Pb-Free Devices

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	40	Vdc
Collector–Base Voltage	$V_{CBO}$	60	Vdc
Emitter–Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current – Continuous	$I_C$	200	mAdc
Electrostatic Discharge	HBM MM	ESD >16000 >2000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

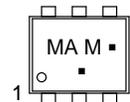


NST3904DXV6T11

### MARKING DIAGRAM



SOT-563  
CASE 463A  
STYLE 1



MA = Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
NST3904DXV6T1G	SOT-563 (Pb-Free)	4000/Tape & Reel
NSVT3904DXV6T1G	SOT-563 (Pb-Free)	4000/Tape & Reel
NST3904DXV6T5G	SOT-563 (Pb-Free)	8000/Tape & Reel
SNST3904DXV6T5G	SOT-563 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NST3904DXV6T1G, NSVT3904DXV6T1G, NST3904DXV6T5G, SNST3904DXV6T5G

## THERMAL CHARACTERISTICS

<b>Characteristic (One Junction Heated)</b>	<b>Symbol</b>	<b>Max</b>	<b>Unit</b>
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$ (Note 1)	$P_D$	357 2.9	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	350	$^\circ\text{C}/\text{W}$
<b>Characteristic (Both Junctions Heated)</b>	<b>Symbol</b>	<b>Max</b>	<b>Unit</b>
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$ (Note 1)	$P_D$	500 4.0	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

1. FR-4 @ Minimum Pad

# NST3904DXV6T1G, NSVT3904DXV6T1G, NST3904DXV6T5G, SNST3904DXV6T5G

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage (Note 2) ( $I_C = 1.0\text{ mAdc}$ , $I_B = 0$ )	$V_{(BR)CEO}$	40	–	Vdc
Collector–Base Breakdown Voltage ( $I_C = 10\text{ }\mu\text{Adc}$ , $I_E = 0$ )	$V_{(BR)CBO}$	60	–	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 10\text{ }\mu\text{Adc}$ , $I_C = 0$ )	$V_{(BR)EBO}$	6.0	–	Vdc
Base Cutoff Current ( $V_{CE} = 30\text{ Vdc}$ , $V_{EB} = 3.0\text{ Vdc}$ )	$I_{BL}$	–	50	nAdc
Collector Cutoff Current ( $V_{CE} = 30\text{ Vdc}$ , $V_{EB} = 3.0\text{ Vdc}$ )	$I_{CEX}$	–	50	nAdc

## ON CHARACTERISTICS (Note 2)

DC Current Gain ( $I_C = 0.1\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 1.0\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 50\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 100\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ )	$h_{FE}$	40 70 100 60 30	– – 300 – –	–
Collector–Emitter Saturation Voltage ( $I_C = 10\text{ mAdc}$ , $I_B = 1.0\text{ mAdc}$ ) ( $I_C = 50\text{ mAdc}$ , $I_B = 5.0\text{ mAdc}$ )	$V_{CE(sat)}$	– –	0.2 0.3	Vdc
Base–Emitter Saturation Voltage ( $I_C = 10\text{ mAdc}$ , $I_B = 1.0\text{ mAdc}$ ) ( $I_C = 50\text{ mAdc}$ , $I_B = 5.0\text{ mAdc}$ )	$V_{BE(sat)}$	0.65 –	0.85 0.95	Vdc

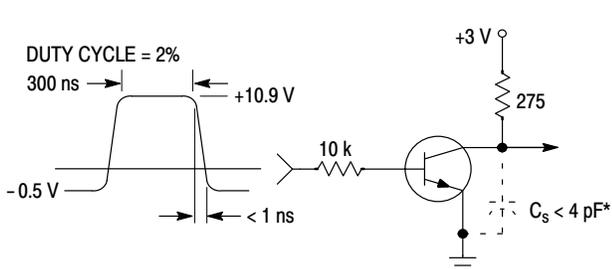
## SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 20\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	300	–	MHz
Output Capacitance ( $V_{CB} = 5.0\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	–	4.0	pF
Input Capacitance ( $V_{EB} = 0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )	$C_{ibo}$	–	8.0	pF
Input Impedance ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 1.0\text{ mAdc}$ , $f = 1.0\text{ kHz}$ )	$h_{ie}$	1.0 2.0	10 12	k $\Omega$
Voltage Feedback Ratio ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 1.0\text{ mAdc}$ , $f = 1.0\text{ kHz}$ )	$h_{re}$	0.5 0.1	8.0 10	$\times 10^{-4}$
Small–Signal Current Gain ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 1.0\text{ mAdc}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	100 100	400 400	–
Output Admittance ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 1.0\text{ mAdc}$ , $f = 1.0\text{ kHz}$ )	$h_{oe}$	1.0 3.0	40 60	$\mu\text{mhos}$
Noise Figure ( $V_{CE} = 5.0\text{ Vdc}$ , $I_C = 100\text{ }\mu\text{Adc}$ , $R_S = 1.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ )	NF	– –	5.0 4.0	dB

## SWITCHING CHARACTERISTICS

Delay Time	( $V_{CC} = 3.0\text{ Vdc}$ , $V_{BE} = -0.5\text{ Vdc}$ )	$t_d$	–	35	ns
Rise Time	( $I_C = 10\text{ mAdc}$ , $I_{B1} = 1.0\text{ mAdc}$ )	$t_r$	–	35	
Storage Time	( $V_{CC} = 3.0\text{ Vdc}$ , $I_C = 10\text{ mAdc}$ )	$t_s$	–	200	ns
Fall Time	( $I_{B1} = I_{B2} = 1.0\text{ mAdc}$ )	$t_f$	–	50	

2. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ ; Duty Cycle  $\leq 2.0\%$ .



\* Total shunt capacitance of test jig and connectors

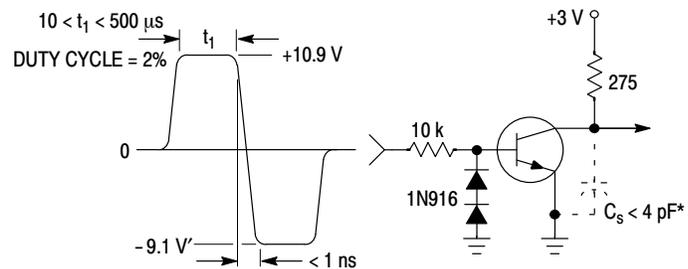


Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

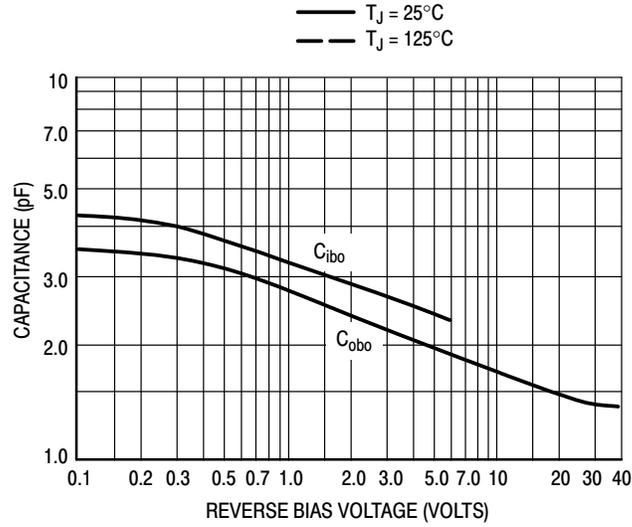


Figure 3. Capacitance

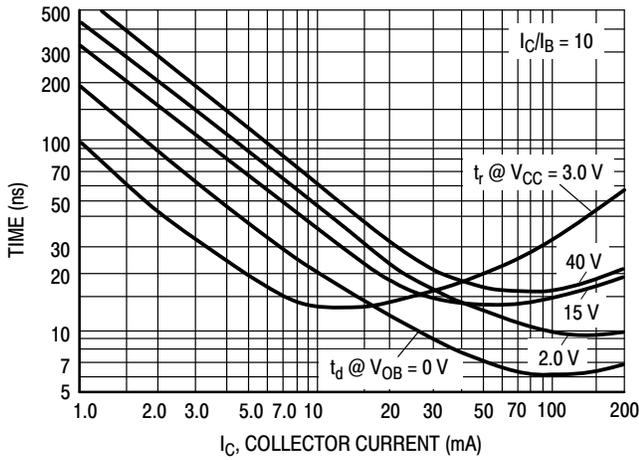


Figure 4. Turn-On Time

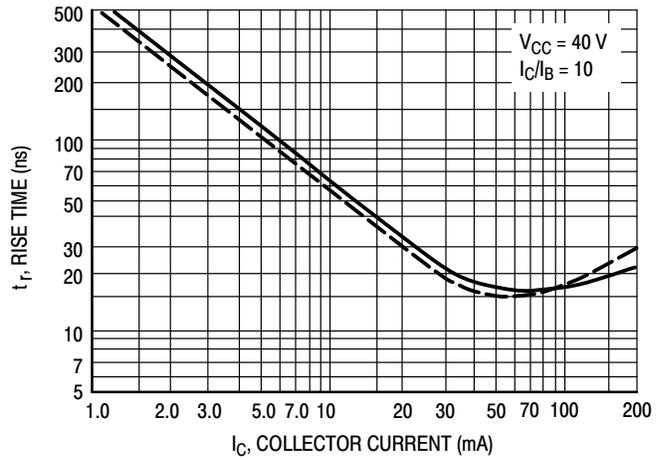


Figure 5. Rise Time

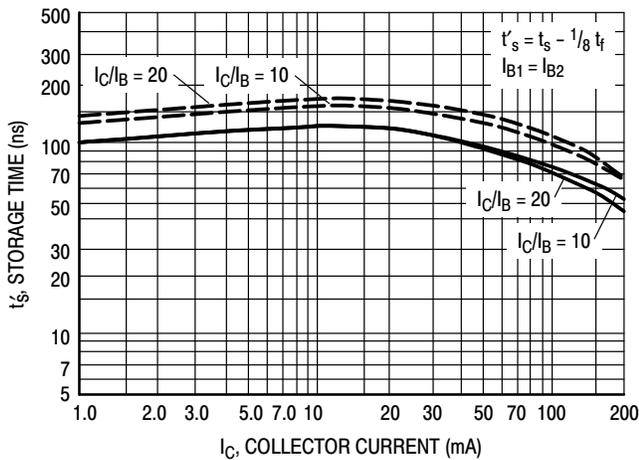


Figure 6. Storage Time

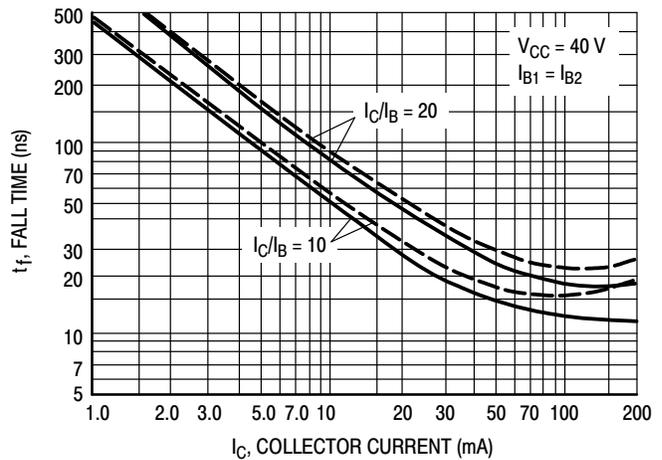


Figure 7. Fall Time

**TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS  
NOISE FIGURE VARIATIONS**

( $V_{CE} = 5.0$  Vdc,  $T_A = 25^\circ\text{C}$ , Bandwidth = 1.0 Hz)

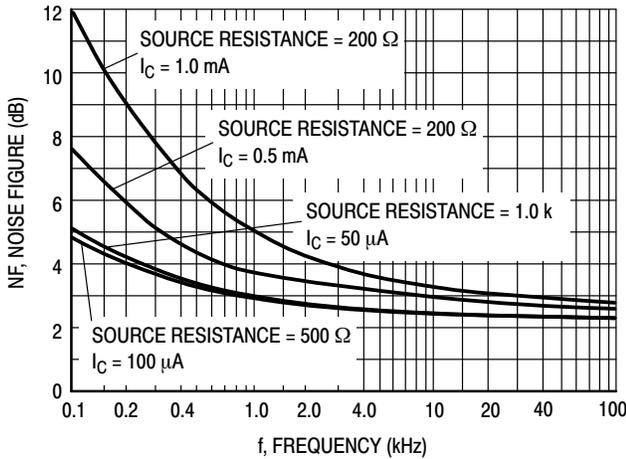


Figure 8. Noise Figure

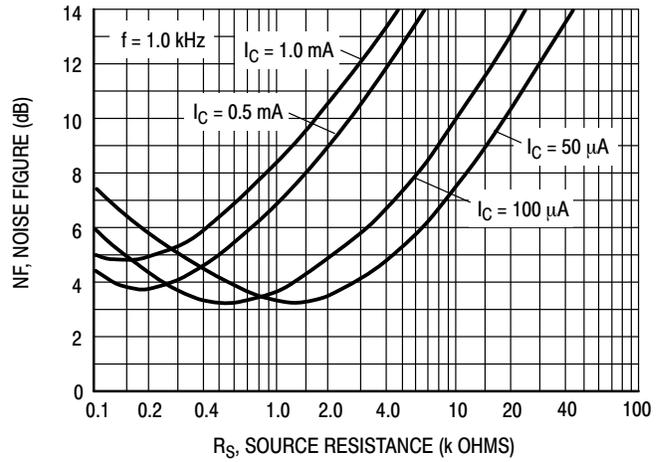


Figure 9. Noise Figure

**h PARAMETERS**

( $V_{CE} = 10$  Vdc,  $f = 1.0$  kHz,  $T_A = 25^\circ\text{C}$ )

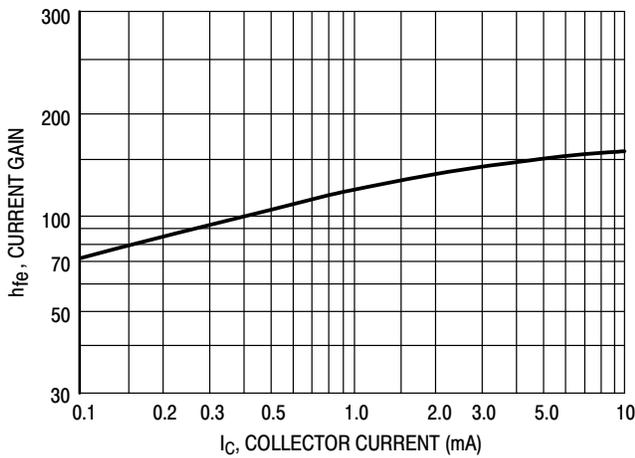


Figure 10. Current Gain

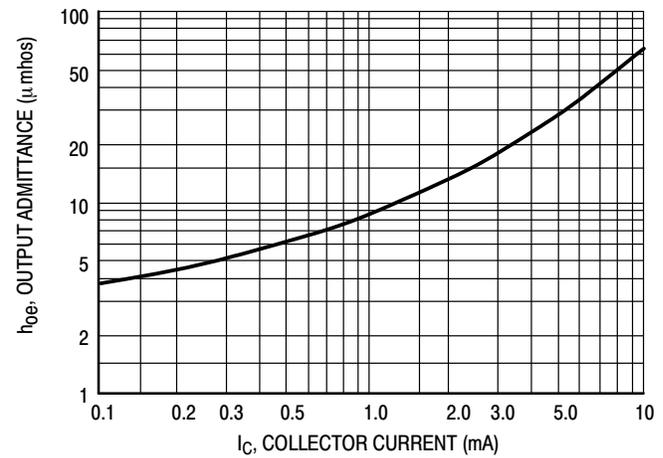


Figure 11. Output Admittance

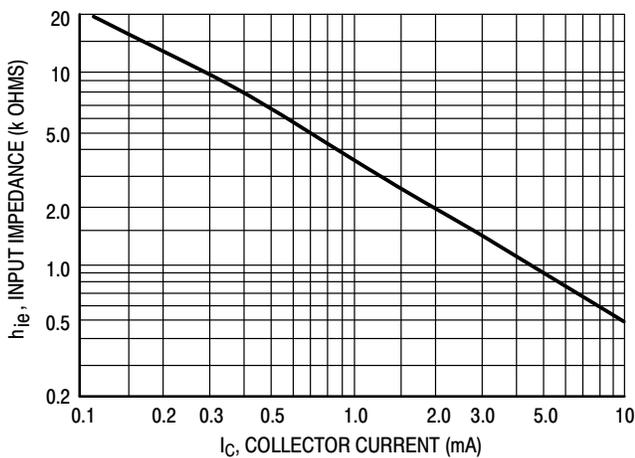


Figure 12. Input Impedance

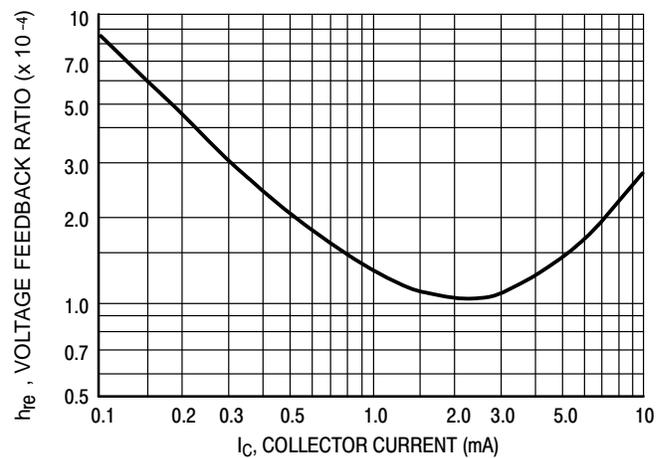


Figure 13. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

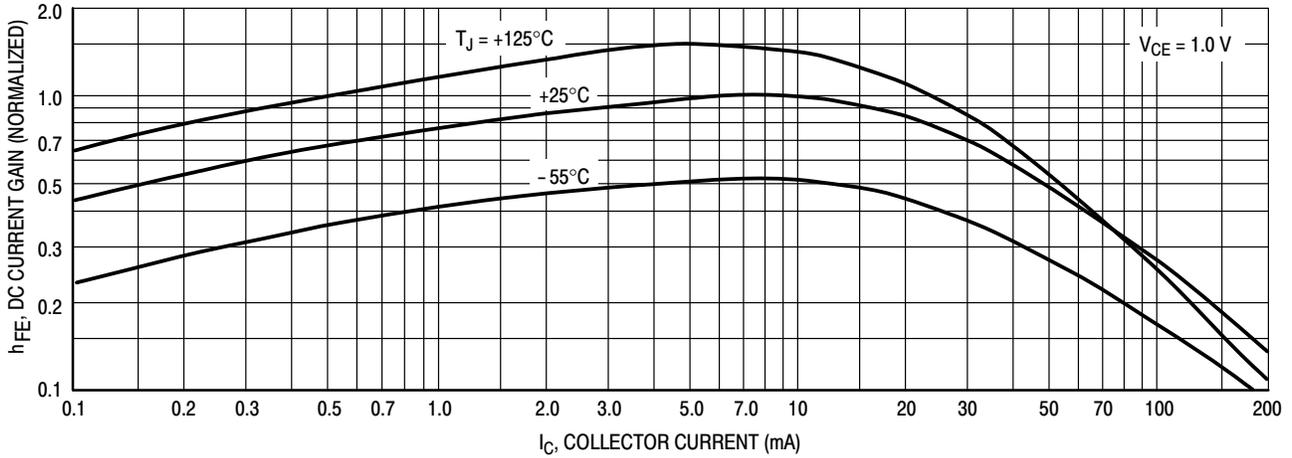


Figure 14. DC Current Gain

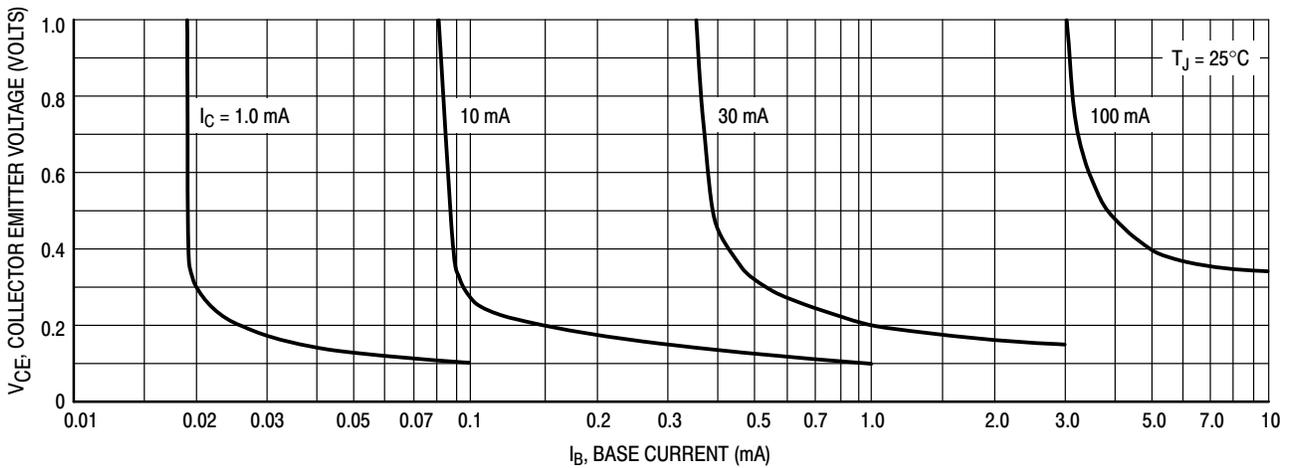


Figure 15. Collector Saturation Region

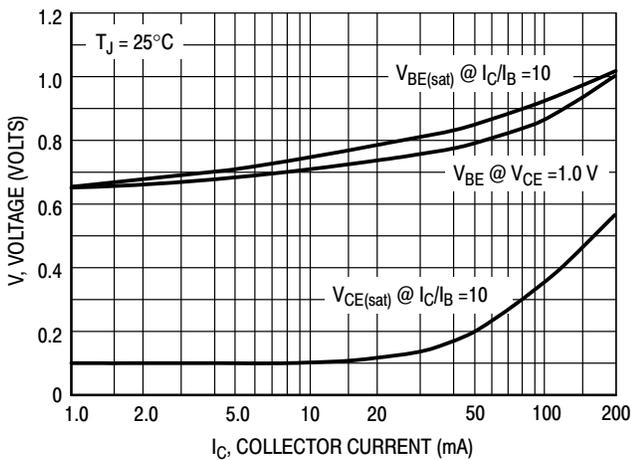


Figure 16. "ON" Voltages

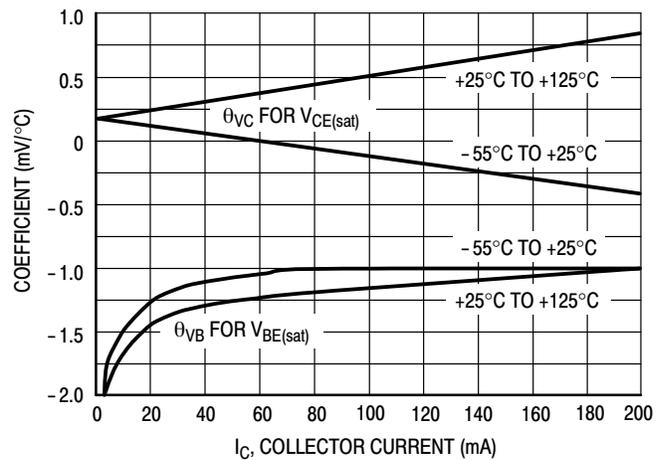
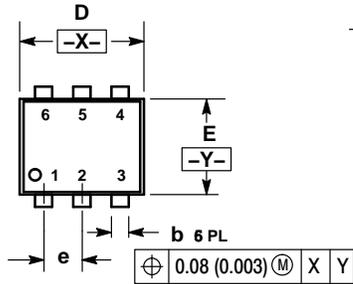


Figure 17. Temperature Coefficients

# NST3904DXV6T1G, NSVT3904DXV6T1G, NST3904DXV6T5G, SNST3904DXV6T5G

## PACKAGE DIMENSIONS

### SOT-563, 6 LEAD CASE 463A ISSUE F

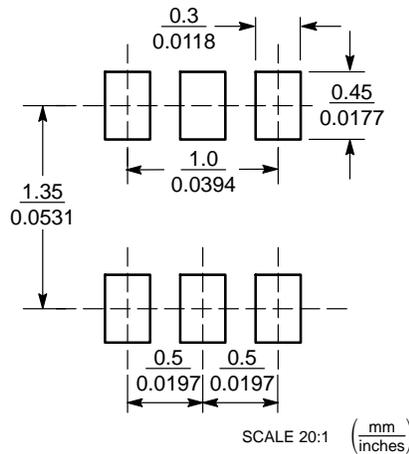


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
C	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
E	1.10	1.20	1.30	0.043	0.047	0.051
e	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H <sub>E</sub>	1.50	1.60	1.70	0.059	0.062	0.066

### SOLDERING FOOTPRINT\*



STYLE 1:

- PIN 1: EMITTER 1  
 2. BASE 1  
 3. COLLECTOR 2  
 4. EMITTER 2  
 5. BASE 2  
 6. COLLECTOR 1

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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